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Manuscript version: Accepted Manuscript
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To cite this article before publication: Gamage et al, 2017, Nanotechnology, at press:
https://doi.org/10.1088/1361-6528/aa7532

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Reliable Passivation of Black Phosphorus by Thin Hybrid Coating

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Black phosphorus (BP) possesses several extraordinary physical properties, which include in-plane anisotropy, thickness dependent direct bandgap and high carrier mobility. These physical properties make BP highly desirable from the point of view of fundamental science and modern optoelectronics applications. The excitement about this material has always been accompanied by unreserved skepticism due to its extraordinary degradation under ambient conditions. Here we show ambient degradation of exfoliated BP can be effectively suppressed using thin layer of hybrid MOCVD coating of BN followed by ALD coating of Al\textsubscript{2}O\textsubscript{3}. We have extensively studied the time dependent, optical and electrical properties of BP encapsulated by BN and/or Al\textsubscript{2}O\textsubscript{3}, using nanoscale infrared imaging and I-V characterizations. Our results show hybrid thin layer (~5 nm) BN/Al\textsubscript{2}O\textsubscript{3} coated BP exfoliated on SiO\textsubscript{2} substrate is protected from degradation in ambient for over 6 months, much longer than those coated only by BN or Al\textsubscript{2}O\textsubscript{3} layers. Our theoretical modeling of the experimental degradation growth pattern shows that the influence of neighboring elements on the degradation of a given element is minimal for BP flakes with hybrid coating. Electrical characterization further confirms the effectiveness of BN/Al\textsubscript{2}O\textsubscript{3} as encapsulation layer and gate dielectrics with minor changes after several weeks.

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1. Introduction

Since the first exfoliation of graphene\cite{1}, several two dimensional (2D) van der Waals materials have been identified and studied\cite{2}. Aside from being excellent host of new physics, these materials promise various potential applications in modern optics and electronics. Among recently isolated layered materials, black phosphorus (BP) stands out as an important material with many unique physical properties such as tunable bandgap in the visible-near infrared wavelength region\cite{3, 4} and in-plane anisotropy that promise novel applications in extensive areas such as field effect transistors (FET)\cite{5}, photodetectors\cite{6}, photoconductive switches\cite{7}.

A significant problem that limits applications of BP is its rapid degradation rate under ambient conditions. Over the last 2-3 years the scientific community has aggressively pursued to understand, avoid and protect the degradation problem in many innovative ways \cite{8-12}. BP’s susceptibility to degradation has been related to its unstable bonding structure arising from the free lone pairs of phosphorus atoms \cite{8, 13}. The rate of oxidation of BP depends on oxygen concentration, light intensity and energy gap has also been investigated\cite{14}. BP oxidation has also been proposed to be caused by a synergistic effect of water and oxygen where water drives the oxidation via the reaction with the surface oxide which then creates oxygen dissociations\cite{15}. Various methods have been investigated by researchers to overcome or slow the degradation of BP with notable degree of success. These include organic coatings and organic covalent/non-covalent functionalization\cite{11, 12, 16, 17}, inorganic coatings\cite{10, 12, 18-20} and a combination of organic and inorganic coatings\cite{21}. We recently studied the degradation of BP extensively by a combination of nanoscale imaging and theoretical modeling, and showed that thick (10 nm or more) Al\textsubscript{2}O\textsubscript{3} coatings can protect BP from ambient degradation.\cite{22} However, finding experimental approaches to reduce the degradation rate with thinner coatings is still a challenge. In this work, we show that a hybrid MOCVD deposited < 2 nm BN layer followed by 3 nm Al\textsubscript{2}O\textsubscript{3} grown using ALD can completely protect BP from degradation for over 6 months.

2. Results and Discussion

BP flakes were transferred onto pre-cleaned Si and SiO\textsubscript{2} substrates using conventional mechanical
exfoliation. Thin layer of boron nitride (BN) and/or Al₂O₃ were then deposited using metal-organic chemical vapor deposition (MOCVD) and atomic layer deposition (ALD) techniques respectively. Four BP samples were prepared with different coatings and substrates. (i) BP flakes on Si wafer covered by 1.6 nm thin BN layer, (ii) BP flakes on SiO₂ substrate coated with 1.6 nm BN layer, and (iii) BP flakes on SiO₂ substrate coated with 1.6 nm thick BN followed by 4 nm thick Al₂O₃. All samples were kept in ambient condition at 22°C with relative humidity ~40%. Topographic and near-field infrared images were taken using a commercial scattering type Scanning Near-Field Optical Microscopy (sSNOM) microscope described in our earlier BP degradation studies [22]. s-SNOM provides topography and infrared near-field images of BP flakes allowing investigation of the degradation evolution and effectiveness of coatings. For revealing the electrical properties of these encapsulated BP layers, a p-channel metal-oxide field-effect transistor (pMOSFET) structure was fabricated using 8 nm BP flake with 200 nm channel length (L) and with BN/Al₂O₃ as gate dielectric. Details of pMOSFET device fabrication and electrical measurement procedures can be found in earlier publication [23].

**Figure 1.** The topography (grey-white) and 3rd harmonic near-field amplitude, A₃ (red-yellow) images of BP on Si (a and d) and SiO₂ (b, c, e, f, g and h) substrates. The flakes are encapsulated by BN (a, b, d and e), hybrid coating of BN-Al₂O₃ (c and f), and by Al₂O₃ (g and h) layers. Scale bar 500 nm.
Figure 1 shows topography and third harmonic near-field amplitude ($A_3$) images of eight BP flakes. Those are with thicknesses ~30 nm (Fig. 1 a, b and c), ~8 nm (Fig. 1 d, e and f), ~5 nm (Fig. 1 g) and ~15 nm (Fig. 1 h). To study the effect of substrates we exfoliated BP on Si and SiO$_2$ substrates. All exfoliated samples were passivated with either BN (Fig. 1 a, b, d and e), hybrid BN-Al$_2$O$_3$ (Fig. 1 c and f) or Al$_2$O$_3$ (Fig. 1 g and h) coatings. We took successive images of all samples shown in Fig. 1 for over 6 months but only displayed certain selected images from each flake for comparison.

As shown in Figure 1-a, b, d & e 1.6 nm BN coating is robust and protects degradation in both the 8 nm and 30 nm thick flakes till about ~at day 11 since exfoliation. After the 11$^{th}$ day, the 8 nm thick flake raptures the BN coating and begins to degrade forming bubbles that grow in size as a function of time. Whereas the 30 nm thick BP flake begins with small bubbles that enlarge with time after the 11$^{th}$ day. The rate of degradation is much slower in 30 nm thick BP flake compared to 8 nm flake of the same coating. BN coating keeps the BP flakes intact regardless of thickness for 11 days we monitored and the degradation afterwards proceeds at much slower rate compared to uncoated BP. We have shown two Al$_2$O$_3$ coated BP flakes of thickness 5 nm (Fig. 1 g) and 15 nm (Fig. 1 h). The Al$_2$O$_3$ coating layer for these two are 1 nm and 5 nm, respectively. The 5 nm flake coated with 1 nm Al$_2$O$_3$ degraded rapidly and ruptured by day 16. However, the 5 nm Al$_2$O$_3$ coating of 15 nm thick flake has decelerated the degradation process significantly, but sporadically evolved bubbles were prominent by day 65. A detailed account on the effect of Al$_2$O$_3$ coating of BP has been given in our previous article [22]. Other studies of BN-BP-BN sandwiched stable heterostructures have been reported before, however the degradation of BP was not monitored beyond a week to assess the effectiveness of the coating [10].

Hybrid BN (1.6 nm thick) plus Al$_2$O$_3$ (3 nm thick) coated BP flakes of thickness 8 nm and 30 nm are shown in Figure 1-c & f. Over the time span of our measurement (over 6 months) the 30 nm BP flake did not show any sign of degradation. The thinner 8 nm double coated flake showed no degradation for over two weeks and starts to show minor degradation which increased very slowly till day 45 as shown in Figure 1-f. Our results unequivocally show that hybrid BN (MOCVD) and Al$_2$O$_3$ (ALD) coating completely avoids degradation of BP flakes for thickness ~30 nm for over 6 months and significantly slows down degradation for thinner (~8 nm thick) BP flakes over a period of a month and half.
Figure 2. The topography (grey-white) and 3rd harmonic near-field amplitude (red-yellow) images of the flakes of Si/BP/BN with thickness ~30 nm (a) and ~8 nm (c) and flakes of SiO$_2$/BP/BN with thickness ~30 nm (b) and ~8 nm (d) on day 7 and day 39. Scale bar 500 nm.

We have also investigated the effect of the substrate on which BP flakes are exfoliated on the degradation. Figure 2 shows the topography and near-field amplitude of two BP flakes (thickness 8 nm and 30 nm) exfoliated on Si and SiO$_2$ substrates and both covered by 1.6 nm BN. These images show that both the 8 nm and 30 nm thick flakes exfoliated on Si wafer show larger degraded area in a similar duration to those exfoliated on SiO$_2$. When the height of the tallest degradation ‘bubble’ on thicker flakes of these two samples are compared, it shows that the bubble height of the flake on SiO$_2$ is ~50% smaller than that of the flake on the Si substrate. Both the area coverage and the volume of the degraded bubbles suggest that BP exfoliated on SiO$_2$ substrate degrades at a slower rate. These results further suggest that it is important to select not only coating material but also the substrate on which to exfoliate/grow BP to reduce degradation [10]. We also note the near-field contrast of BP on Si substrate is larger than that on SiO$_2$ due to the larger permittivity of Si ($\varepsilon_{\text{Si}}>\varepsilon_{\text{BN}}>\varepsilon_{\text{SiO}_2})$. 
We implemented a model developed in our previous work in Ref[22] to understand the evolution of the degradation process of the samples investigated experimentally. In this model, the sample surface is divided into \( N \times N \) square elements that were randomly defined to be in degraded or non-degraded state. For each of these elements, the number of degraded neighboring elements, \( n; (0 < n < 8) \) were correlated to the degradation probability of the considered element. We considered two cases (i) inclusion, and (ii) exclusion of the influence of neighboring elements on the degradation of a given element. Experimental data in our previous study well fitted with model that considers case (i) where inclusion of the influence of neighbors was a considerable factor [22]. In our present experiment we found that as the passivation becomes more robust such as using hybrid coating, the evolution of percent degradation as a function of time does not depend on the influence of neighbors as described further below.

In Fig. 3 we show in blue circles the degradation area percentage as function of time extracted from the experiments for each of the six flakes described in Fig. 1 and discussion thereof. The red lines in Fig. 2 show the fitting result of percent degradation of each flake, based on our theoretical model[22]. Of all the samples studied, both 8 nm and 30 nm thick BP flakes exfoliated on Si wafer and coated only with BN layer are the samples with highest rate of degradation. As shown in Fig. 2a & d, for these samples the model that considers inclusion of influence of the neighboring elements on the degradation (case i) agrees well with the experimental data. However, for the flakes with slower degradation, fitting significantly failed to represent the experimental results when neighbor influence is considered in calculations. Surprisingly, when the neighbor influence is excluded in calculations the model fitted the experimental data in a very good agreement as shown in Fig. 2b,c &e resulting in an almost-linear relationship between degradation area percentage and time. This behavior suggests that the neighbor influence on degradation of a given site is significantly suppressed in the SiO\(_2\)/BP/BN and SiO\(_2\)/BP/BN/Al\(_2\)O\(_3\) samples. Moreover, according to the topography and near-field amplitude images shown in Fig. 1f, and degradation % vs. time in Fig. 2f, the 30 nm flake on SiO\(_2\) coated with BN and Al\(_2\)O\(_3\) shows significantly protected from degradation. We also note thickness dependent degradation of BP has been explained recently by the decrease in bandgap with increasing layer thickness that leads to decrease in oxygen acceptance rate [17].
The output characteristics of the drain current ($I_d$) vs. drain voltage ($V_d$) of a BN/Al$_2$O$_3$ top-gate BP MOSFET the device are shown in Fig. 4a. The highest drain current, $I_d = 800 \mu$A/μm was achieved at $V_d = -1.6$ V and gate voltage, $V_g = -4$ V. The low contact resistance and high hole mobility of BP lead to the high on-state drain current of this device. However, due to the narrow bandgap of BP, the electron Schottky barrier is low in general, in great contrast to transition metal dichalcogenides such as MoS$_2$, ambipolar effect degrades the off-state of the device, which leads to a significant current at large drain voltage. In order to study how the device performance changes with time, the $I_d$-$V_g$ transfer characteristics measurements were performed after fabrication, and after 14 days and 28 days stored in nitrogen box, with $V_d = -0.1$ V. These time dependent $I_d$-$V_g$ curves are presented in Fig. 4b. Even after 28 days, the device still worked with small changes at off-state such as a minor shift in threshold voltage observed on day 14 and day 28 curves. Without BN/Al$_2$O$_3$ encapsulation, the device is hard to survive over 24 hours due to the strong chemical reaction of BP with moisture in ambient [14,24]. The electrical characterizations are also consistent with the surface analysis described above.

In summary, based on both surface analysis and electrical measurements, we have shown that the surface stability of BP can be significantly improved by a hybrid ~5nm coating of BN/Al$_2$O$_3$. Even after 6 months, no sign of surface degradation was observed on ~30 nm BP flake. The electrical properties of pMOSFET device structure with BN/Al$_2$O$_3$ as gate produced excellent drain current of 800 $\mu$A/μm promising the use of this technique for further development of BP based electrical devices.

Acknowledgements
The work was supported by a grant from the Air Force Office of Scientific Research (AFOSR) grant number FA9550-16-1-0172. S.G. and N.A. acknowledge support provided by National Science Foundation grant no. 1553251. The authors would like to thank Mike Snure and Qing Paduano from AFRL, Wright-Patterson AFB providing us the high-quality of MOCVD BN films.
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